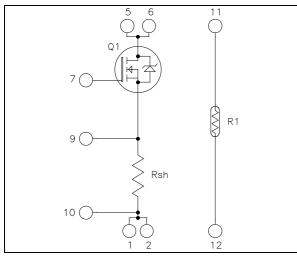
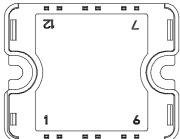


## Linear MOSFET Power Module





Pins 1/2; 5/6 must be shorted together

# $$\begin{split} V_{DSS} &= 600V \\ R_{DSon} &= 125 m\Omega \text{ typ } @ \text{ Tj} = 25^{\circ}\text{C} \\ I_D &= 45 \text{A*} @ \text{ Tc} = 25^{\circ}\text{C} \end{split}$$

#### **Application**

• Electronic load dedicated to power supplies and battery discharge testing

#### **Features**

- Linear MOSFET
- Very low stray inductance
- Internal thermistor for temperature monitoring
- High level of integration
- AlN substrate for improved thermal performance

#### **Benefits**

- Direct mounting to heatsink (isolated package)
- easy series and parallels combinations for power and voltage improvements
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

#### Absolute maximum ratings

| Symbol            | Parameter   |                     | Max ratings | Unit      |
|-------------------|---|---------------------|-------------|-----------|
| $V_{ m DSS}$      | Drain - Source Breakdown Voltage                        |                     | 600         | V         |
| Ţ                 | Continuous Drain Current                                | $T_c = 25^{\circ}C$ | 45*         |           |
| $I_D$             | Continuous Diam Current                                 | $T_c = 80$ °C       | 33*         | A         |
| $I_{DM}$          | Pulsed Drain current                                    |                     | 172         |           |
| $V_{GS}$          | Gate - Source Voltage                                   |                     | ±30         | V         |
| R <sub>DSon</sub> | Drain - Source ON Resistance                            |                     | 150         | $m\Omega$ |
| $P_{D}$           | Maximum Power Dissipation $\bullet$ $T_c = 25^{\circ}C$ |                     | 568         | W         |
| $I_{AR}$          | Avalanche current (repetitive and non repetitive)       |                     | 45          | A         |
| $E_{AR}$          | Repetitive Avalanche Energy                             |                     | 50          | mJ        |
| $E_{AS}$          | Single Pulse Avalanche Energy                           |                     | 3000        | 1113      |

- \* Output current must be limited to 31A @ T<sub>C</sub>=25°C and 22A @ T<sub>C</sub>=80°C to not exceed the shunt specification.
- In saturation mode

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

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#### All ratings @ $T_i = 25$ °C unless otherwise specified

#### **Electrical Characteristics**

| Symbol              | Characteristic                  | Test Conditions                          |                     | Min | Typ | Max  | Unit |  |
|---------------------|---------------------------------|--|---------------------|-----|-----|------|------|--|
| $I_{DSS}$           | Zero Gate Voltage Drain Current | $V_{DS} = 600V ; V_{GS} = 0V$            | $T_j = 25^{\circ}C$ |     |     | 25   | 1    |  |
|                     |                                 | $V_{DS} = 480V ; V_{GS} = 0V$            | $T_j = 125$ °C      |     |     | 250  | μA   |  |
| R <sub>DS(on)</sub> | Drain – Source on Resistance    | $V_{GS} = 10V, I_D = 22.5A$              |                     |     | 125 | 150  | mΩ   |  |
| V <sub>GS(th)</sub> | Gate Threshold Voltage          | $V_{GS} = V_{DS}, I_{D} = 2.5 \text{mA}$ |                     | 2   |     | 4    | V    |  |
| $I_{GSS}$           | Gate – Source Leakage Current   | $V_{GS} = \pm 30 \text{ V}$              | •                   |     |     | ±100 | nA   |  |

**Dynamic Characteristics** 

| Symbol    | Characteristic               | Test Conditions    | Min | Тур  | Max | Unit |
|-----------|------------------------------|--------------------|-----|------|-----|------|
| $C_{iss}$ | Input Capacitance            | $V_{GS} = 0V$      |     | 7600 |     |      |
| $C_{oss}$ | Output Capacitance           | $V_{\rm DS} = 25V$ |     | 1280 |     | pF   |
| $C_{rss}$ | Reverse Transfer Capacitance | f = 1MHz           |     | 620  |     |      |

#### **Shunt Electrical Characteristics**

| Symbol          | Characteristic     |                      | Min | Тур | Max | Unit |
|-----------------|--------------------|----------------------|-----|-----|-----|------|
| $R_{sh}$        | Resistance value   |                      |     | 20  |     | mΩ   |
| $T_{sh}$        | Tolerance          |                      |     | 2   |     | %    |
| $P_{\rm sh}$    | L L Oad Canacity   | $T_{\rm C}$ =25°C    |     |     | 20  | W    |
| r <sub>sh</sub> |                    | T <sub>C</sub> =80°C |     |     | 10  | VV   |
| $I_{sh}$        | Current capacity - | T <sub>C</sub> =25°C |     |     | 31  | ۸    |
|                 |                    | T <sub>C</sub> =80°C |     |     | 22  | A    |

**Temperature sensor PTC** 

| Symbol           | Characteristic          |                   | Min   | Typ   | Max   | Unit  |
|------------------|-------------------------|-------------------|-------|-------|-------|-------|
| R <sub>25</sub>  | Resistance @ 25°C       |                   | 1980  |       | 2020  | Ω     |
| $R_{100}/R_{25}$ | Resistance ratio        | Tamb=100°C & 25°C | 1.676 | 1.696 | 1.716 |       |
| $R_{-55}/R_{25}$ | Resistance ratio        | Tamb=-55°C & 25°C | 0.48  | 0.49  | 0.50  |       |
| В                | Temperature coefficient |                   |       | 7900  |       | ppm/K |

Thermal and package characteristics

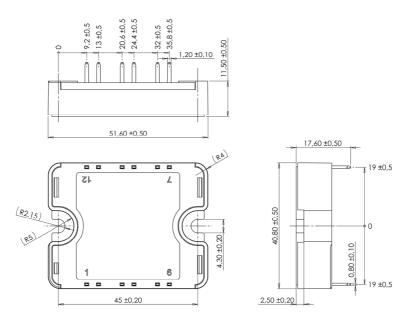
| Symbol      | Characteristic  |             | Min    | Тур | Max | Unit |      |
|-------------|---|-------------|--------|-----|-----|------|------|
| $R_{thJC}$  | Junction to Case Thermal Resistance                           |             | MOSFET |     |     | 0.22 | °C/W |
| $V_{ISOL}$  | RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz |             | 4000   |     |     | V    |      |
| $T_{J}$     | Operating junction temperature range                          |             | -40    |     | 150 |      |      |
| $T_{STG}$   | Storage Temperature Range                                     |             | -40    |     | 125 | °C   |      |
| $T_{\rm C}$ | Operating Case Temperature                                    |             |        | -40 |     | 100  |      |
| Torque      | Mounting torque   | To heatsink | M4     | 2   |     | 3    | N.m  |
| Wt          | Package Weight  | •           |        |     |     | 80   | g    |

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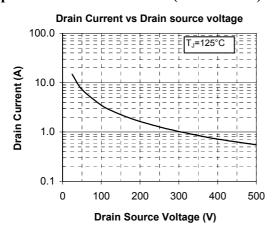


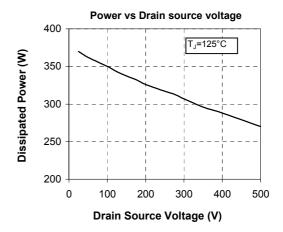
#### SP1 Package outline (dimensions in mm)



See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

#### **Typical Performance Curve (linear mode)**





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